Appl.No.: 10/634,413 Amd. dated 06/10/2005

Response to Office Action of 02/10/2005

## **REMARKS/ARGUMENTS**

Claims 7-10 are pending in the application; reexamination and reconsideration are hereby requested.

Claims 7-10 were previously allowed. However, applicants have recently become aware of further prior art as listed on the enclosed Information Disclosure Statement Form 1449. In particular, applicants note column 22, lines 24-30 of USP 5,707,486 describe a two-step plasma-enhanced deposition of oxide over aluminum interconnect lines with the first step at no bottom bias to deter sputtering of the aluminum. In contrast, Claims 7-10 require deposition over insulated gates; the low bias step is to prevent gate dielectric damage from the antenna effect.

Respectfully submitted,

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